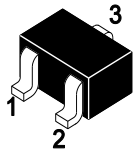
LBSS84WT1G
S-LBSS84WT1G

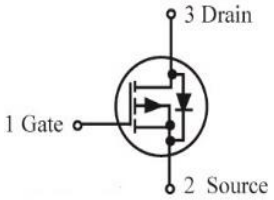
Power MOSFET
130 mAmps, 50 Volts P–Channel SC-70

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Energy efficient



SC70(SOT-323)



2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBSS84WT1G	PD	3000/Tape&Reel
LBSS84WT3G	PD	10000/Tape&Reel

3. MAXIMUM RATINGS(Ta = 25ºC)

Parameter	Symbol	Limits	Unit
Drain–Source Voltage	VDSS	-50	Vdc
Gate–to–Source Voltage – Continuous	VGS	±20	Vdc
Drain Current – Continuous TA = 25°C – Pulsed (tp≤10μs)	 ID IDM	 -130 -520	mAdc

4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR−5 Board (Note 1) @ TA = 25ºC Derate above 25ºC	PD	225 1.8	mW mW/ºC
Thermal Resistance, Junction–to–Ambient(Note 1)	RΘJA	556	ºC/W
Junction and Storage temperature	TJ,Tstg	−55~+150	° C
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	TL	260	ºC

1. FR–5 = 1.0×0.75×0.062 in.

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Drain–Source Breakdown Voltage (VGS = 0, ID = -250μAdc)	VBRDSS	-50	-	-	Vdc
Zero Gate Voltage Drain Current	IDSS				μAdc
(VGS = 0, VDS = -25 Vdc)		-	-	-0.1	
(VGS = 0, VDS = -50 Vdc)		-	-	-15	
(VGS = 0, VDS = -50 Vdc,TJ=125°C)		-	-	-60	
Gate–Body Leakage Current, Forward (VGS = 20 Vdc)	IGSSF	-	-	10	μAdc
Gate–Body Leakage Current, Reverse (VGS = - 20 Vdc)	IGSSR	-	-	-10	μAdc

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage (VDS = VGS, ID = -250μAdc)	VGS(th)	-0.8	-	-2	Vdc
Static Drain–Source On–State Resistance (VGS = -5.0 Vdc, ID = -100 mAdc)	RDS(on)	-	5	10	Ohms
Transfer Admittance (VDS = -25 Vdc, ID = -100 mAdc, f = 1.0 kHz)	|yfs|	50	-	-	mS

DYNAMIC CHARACTERISTICS

Input Capacitance (VDS = -5.0 Vdc)	Ciss	-	30	-	pF
Output Capacitance (VDS = -5.0 Vdc)	Coss	-	10	-	pF
Reverse Transfer Capacitance (VDS = -5.0 Vdc)	Ciss	-	5	-	pF

SWITCHING CHARACTERISTICS

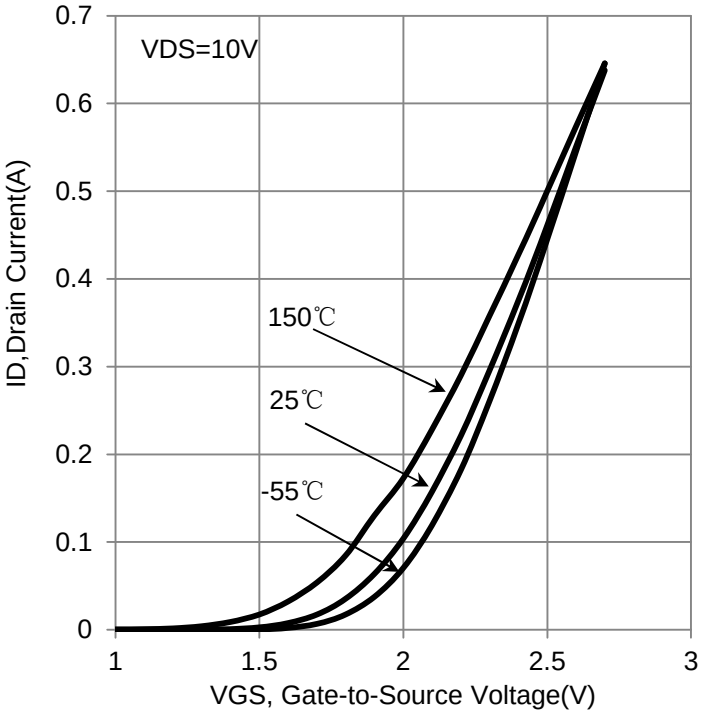
Turn-On Delay Time	(VDD = –15 Vdc, ID = –2.5 Adc,RL = 50 Ω)	td(on)	-	2.5	-	ns
Rise Time		tr	-	1	-	
Turn-Off Delay Time		td(off)	-	16	-	
Fall Time		tf	-	8	-	

SOURCE–DRAIN DIODE CHARACTERISTICS

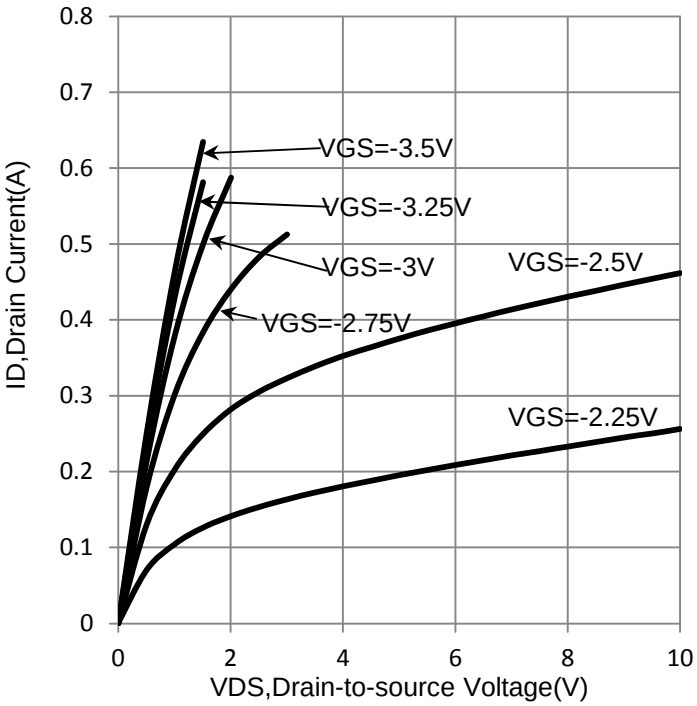
Continuous Current	IS	-	-	-0.13	A
Pulsed Current	ISM	-	-	-0.52	A
Forward Voltage	VSD	-	-2.5	-	V

2.Pulse Test: Pulse Width ≤300 μs, Duty Cycle ≤2.0%.

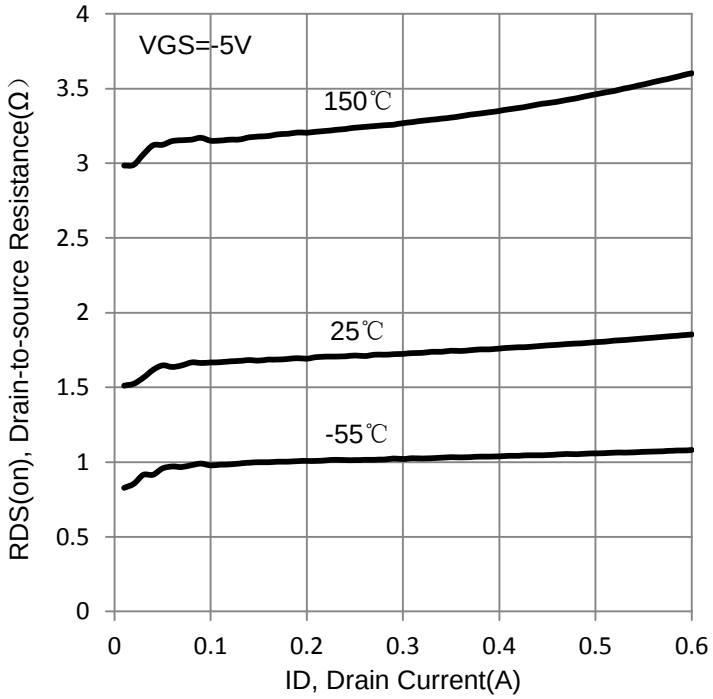
6. ELECTRICAL CHARACTERISTICS CURVES



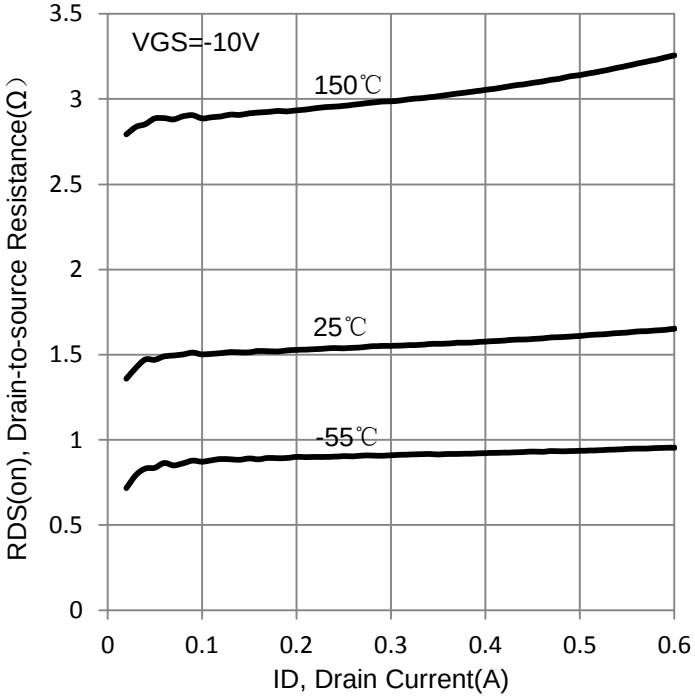
Transfer Characteristics



On-Region Characteristics

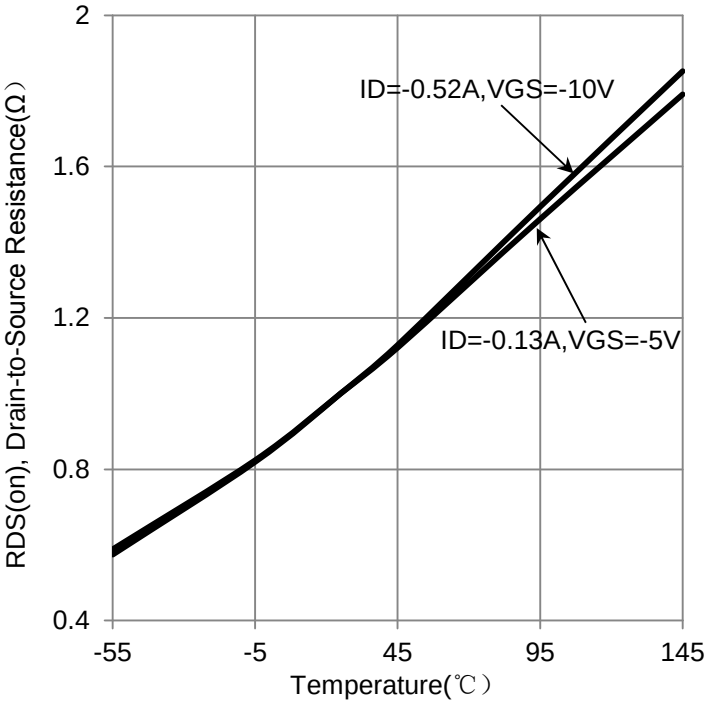


RDS(on) vs. ID

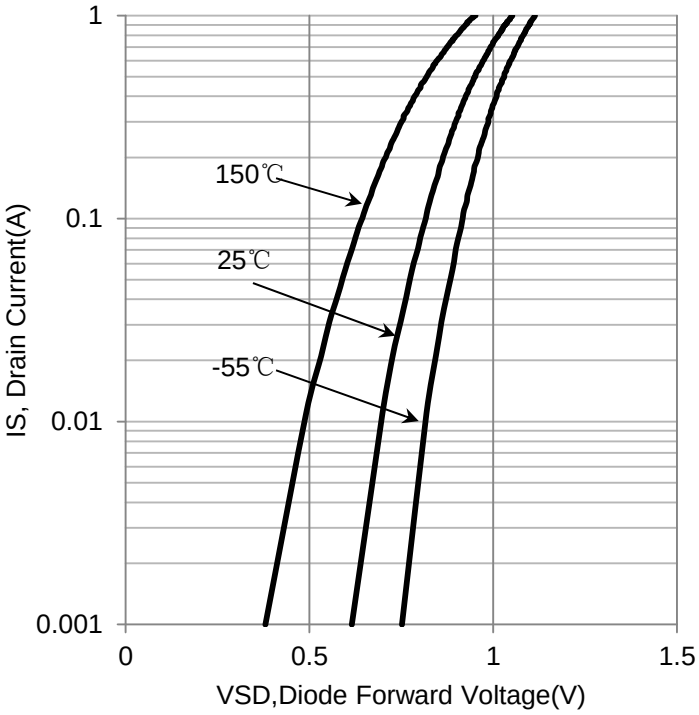


RDS(on) vs. ID

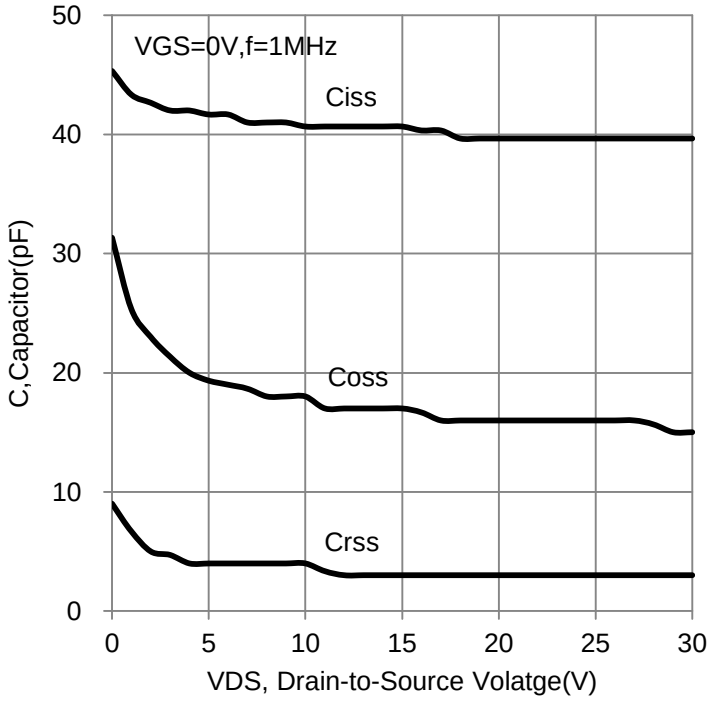
6. ELECTRICAL CHARACTERISTICS CURVES(Con.)



RDS(on) vs. Temperature

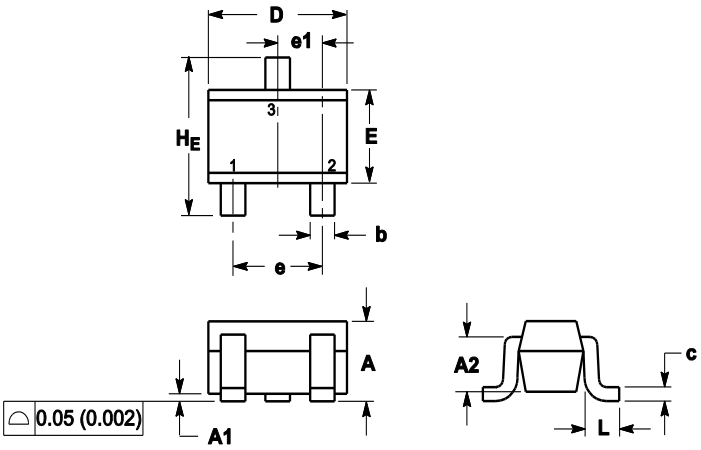


IS vs. VSD



Capacitor vs. VDS

7.OUTLINE AND DIMENSIONS



Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.039
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70REF			0.028REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65REF			0.026REF		
L	0.20	0.38	0.56	0.008	0.015	0.022
H_E	2.00	2.10	2.40	0.079	0.083	0.095

8.SOLDERING FOOTPRINT